

04-SEP-2003 18:21 FROM

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P.02

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicants: Chen, *et al.* Attorney Docket: TSM6283131RI
Serial No. TBD Filed: Herewith
Reissue of: 6,283,131 B1 Issued: September 4, 2001
Title: IN-SITU STRIP PROCESS FOR POLYSILICON ETCHING IN DEEP SUB-MICRON TECHNOLOGY

Mail Stop Reissue
Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

DECLARATION AND POWER OF ATTORNEY FOR APPLICATION
FOR REISSUE OF U.S. PATENT NO. 6,283,131

Dear Sir:

As a below-named inventor, I hereby declare that:

Pursuant to the requirements of 37 C.F.R. §1.63(a)(3), my residence and country of citizenship are provided below next to my name.

I hereby state that I am the original, first and joint inventor of the subject matter which is described and claimed in U.S. Patent 6,283,131, and of the subject matter which is claimed in the claims in the application for reissue of U.S. Patent 6,283,131, which application is attached hereto.

I hereby state that I have reviewed and understand the contents of the specification, including the claims, as included with this application for reissue.

Pursuant to the requirements of 37 C.F.R. §1.175(a)(1), I believe that U.S. Patent No. 6,283,131 is wholly or partly inoperative by reason of claiming less than I had a right to claim in the patent.

TSM6283131RI

1

04-SEP-2003 18:21 FROM

TO 00219727329218

P.03

At Least One Error under 35 U.S.C. §251 as to the Scope of the Original Claims being Relied on as the Basis for Reissue.

The error involves the failure to claim the invention as broadly as I am entitled. One error upon which reissue is based is the unnecessary limitation in claim 16 of "providing a polysilicon layer." The limitation to a conductive layer being fabricated from polysilicon is not necessary to my invention or to distinguish over the prior art. This error can be corrected by removal of the unnecessary limitation "polysilicon" as per the accompanying amendment to the claims. Other errors are sought to be corrected as well.

Pursuant to requirements of 37 C.F.R. §1.175(a)(2), I state that all errors being corrected in the reissue application up to the time of filing this Declaration arose without any deceptive intention on the part of the Applicant.

Pursuant to requirements of 37 C.F.R. §1.63(b)(3), I acknowledge the duty to disclose to the Office all information known to Applicant to be material to patentability as defined in 37 C.F.R. §1.56.

Pursuant to requirements of 37 C.F.R. §1.68, I declare further that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

I hereby appoint the following individuals as my representatives with full power of substitution and revocation to prosecute a Reissue application upon U.S. Patent No. 6,283,131

TSM6283131R1

2

04-SEP-2003 18:22 FROM

TO 00219727329218

P.04

and to transact all business in the United States Patent and Trademark Office connected therewith:

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